

LNA-IC for 2.1 GHz / 1.9 GHz Band Applications

FEATURES

• Low voltage operation +2.80 V typ.

• High gain 15.5 dB typ. fRX = 2132.5 MHz

15.5 dB typ. fRX = 1960 MHz

• Low noise figure 1.30 dB typ. fRX = 2132.5 MHz

1.30 dB typ. fRX = 1960 MHz

• Low distortion

(IIP3 +10 MHz offset)

+9.5 dBm typ. fRX = 2132.5 MHz +10.0 dBm typ. fRX = 1960 MHz

• 5 pin Plastic Small Surface Mount Package (SMINI Type)

DESCRIPTION

AN26013A is LNA-IC for 1.9GHz -2.5 GHz Band Applications.

Realizing high performance by using 0.18 μm SiGeC Bi-CMOS process(f_T = 90 GHz, f_{max} = 140 GHz).

Low Gain mode is available, controlled by integrated CMOS logic circuit.

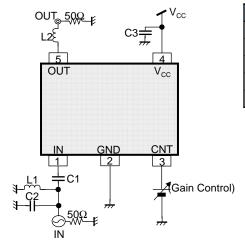
Achieving miniaturization by using small size package.

APPLICATIONS

- ●Cellular Phone 2.1GHz / 1.9GHz Band
- ●WLAN 2.4GHz
- ●WiMAX 2.5GHz

SIMPLIFIED APPLICATION

TOP VIEW



Components	Size	Value	Part Number	Vendor
L1	L1 0603		LQP03T3N0B04	Murata
L2	0603	5.6 nH	LQP03T5N6H04	Murata
C1	0603	1000 pF	GRM033B11C102KD01	Murata
C2	0603	2.0 pF	GJM0334C1E2R0BB01	Murata
C3	0603	0.1 μF	GRM033B30J104KE18	Murata

Notes) This application circuit is an example. The operation of mass production set is not guaranteed. You should perform enough evaluation and verification on the design of mass production set. You are fully responsible for the incorporation of the above application circuit and information in the design of your equipment



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit	Note
Supply voltage	V _{cc}	3.6	V	*1
Supply current	I _{cc}	18	mA	_
Operating ambient temperature	T _{opr}	-20 to +70	°C	*2
Operating junction temperature	T _j	-40 to +125	°C	*2
Storage temperature	T _{stg}	-55 to +125	°C	*2
	IN (Pin No.1)	_	V	*3
Input Voltage Range	CNT (Pin No.3)	- 0.3 to (V _{CC} +0.3)	V	*4
	OUT (Pin No.5)	- 0.3 to (V _{CC} +0.3)	V	*4
ESD	HBM (Human Body Model)	2000	V	_

Notes). This product may sustain permanent damage if subjected to conditions higher than the above stated absolute maximum rating.

This rating is the maximum rating and device operating at this range is not guaranteeable as it is higher than our stated recommended operating range.

When subjected under the absolute maximum rating for a long time, the reliability of the product may be affected.

POWER DISSIPATION RATING

PACKAGE	θ _{JA}	PD (Ta=70 °C)	
SSMINI-5DC	833°C/W	0.12W	0.066W

Note). For the actual usage, please refer to the PD-Ta characteristics diagram in the package specification, supply voltage, load and ambient temperature conditions to ensure that there is enough margin follow the power and the thermal design does not exceed the allowable value.



CAUTION

Although this has limited built-in ESD protection circuit, but permanent damage may occur on it. Therefore, proper ESD precautions are recommended to avoid electrostatic damage to the MOS gates

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min.	Тур.	Max.	Unit	Note
Supply voltage range	V _{cc}	2.65	2.8	2.95	V	*1

Note) *1: The values under the condition not exceeding the above absolute maximum ratings and the power dissipation

^{*1:}The values under the condition not exceeding the above absolute maximum ratings and the power dissipation.

^{*2:}Except for the operating ambient temperature, operating junction temperature and storage temperature, all ratings are for Ta = 25°C.

^{*3:}RF signal input pin. Do not apply DC. Do not apply more than 0 dBm to RF input.

^{*4:(}Vcc + 0.3) V must not be exceeded 3.6 V.



ELECRTRICAL CHARACTERISTICS

Note) $V_{CC} = 2.80 \text{ V}$, $T_a = 25^{\circ}\text{C}\pm2^{\circ}\text{C}$, unless otherwise specified. Performance based on application circuit 1 on page 10.

	Daramatar	Cumbal	Conditions		Limits		Unit	Note
	Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
DC	electrical characteristics							
	Supply current (High Gain Mode)	IccHS	Vcc current at High Gain mode No input signal	_	10	13.5	mA	_
	Supply current (Low Gain Mode)	IccLS	Vcc current at Low Gain mode No input signal	_	1	10	μА	_
	CNT current (High Gain Mode)	IcntHS	Current at CNT Pin Voltage at CNT Pin = 2.80 V	_	2	35	μА	_
	CNT current (Low Gain Mode)	IcntLS	Current at CNT Pin Voltage at CNT Pin = 0 V	_	1	10	μА	_
	CNT voltage (High Gain Mode)	VIHS	_	2.52	_	Vcc + 0.3	V	_
	CNT voltage (Low Gain Mode)	VILS	_	-0.3	_	0.3	V	_



ELECRTRICAL CHARACTERISTICS (continued)

Note) Vcc = 2.80 V,

 $Ta = 25^{\circ}C \pm 2^{\circ}C$, fRX = 2132.5 MHz, PRX = -30 dBm, CW unless otherwise specified.

Performance based on application circuit 1 on page 10.

	Davamatav	Symbol	Symbol Conditions		Limits			Note		
	Parameter	raianietei Symbol Conditions		Min	Тур	Max	Unit	Note		
LNA	NA AC electrical characteristics (High Gain Mode)									
	Power Gain HG	GHSa	_	13.5	15.5	17.5	dB	_		
	IIP3 +10 MHz offset	IIP3Sa	f1 = fRXa + 10 MHz f2 = fRXa + 20 MHz Input 2 signals (f1, f2)	6.0	9.5	_	dBm	_		
LNA	LNA AC electrical characteristics (Low Gain Mode)									
	Power Gain LG	GLSa	PRXa = -20 dBm	-9.5	-7.5	-5.5	dB	_		



APPLICATION INFORMATION REFERENCE VALUES FOR DESIGN

Note) Vcc = 2.80 V

 $Ta = 25^{\circ}C \pm 2^{\circ}C$, fRXa = 2110 MHz, 2132.5 MHz, 2155 MHz, PRXa = -30 dBm, CW unless otherwise specified. Performance based on application circuit 1 on page 10.

Downwater	Complete	Conditions	Refe	rence v	alues	l lmit	Note
Parameter	Symbol	Conditions	Min	Тур	Max	Unit	Note
LNA AC electrical characteristics	(High Gain	Mode)					
Power Gain HG	GHa	_	13.5	15.5	17.5	dB	*1
Noise Figure HG	Noise Figure HG NFHa		_	1.3	1.9	dB	*1
IIP3 +10 MHz offset HG	IIP3H1a	f1 = fRXa + 10 MHz f2 = fRXa + 20 MHz Input 2 signals (f1, f2)	6.0	9.5	_	dBm	*1
IIP3 -10 MHz offset HG	IIP3H2a	f1 = fRXa - 10 MHz f2 = fRXa - 20 MHz Input 2 signals (f1, f2)	6.0	9.5		dBm	*1
Input P1dB	IP1dBa	_	-15.0	-10.0	_	dBm	*1
Reverse Isolation HG	ISOHa	_	_	-30.0	-25.0	dB	*1
Input Return Loss HG	S11Ha	_	5.5	8.0	_	dB	*1
Output Return Loss HG	S22Ha	_ 10		13.0	_	dB	*1
LNA AC electrical characteristics	(Low Gain	Mode)					
Power Gain LG	GLa	PRXa = - 20 dBm	-9.5	-7.5	-5.5	dB	*1
Noise Figure LG	NFLa	_	_	7.5	10.0	dB	*1
IIP3 +10 MHz offset LG	IIP3L1a	f1 = fRXa + 10 MHz f2 = fRXa + 20 MHz PRXa = -10 dBm Input 2 signals (f1, f2)	20.0	24.0	_	dBm	*1
Reverse Isolation LG	ISOLa	_	-9.5	-7.5	-5.5	dB	*1
Input Return Loss LG	S11La	_	4.0	6.0	_	dB	*1
Output Return Loss LG	S22La	_	11.0	15.0	_	dB	*1

Note) *1 : Checked by design, not production tested.



Note) Vcc = 2.80 V

 $Ta = 25^{\circ}C \pm 2^{\circ}C$, fRXb = 1930 MHz, 1960 MHz, 1990 MHz, PRXb = -30 dBm, CW unless otherwise specified. Performance based on application circuit 2 on page 10.

Damanatan	0	O - m distinue	Refe	rence va	alues	I Imit	Nata
Parameter	Symbol	Conditions	Min	Тур	Max	Unit	Note
LNA AC electrical characteristics	(High Gain	Mode)					
Power Gain HG	GHb	_	13.5	15.5	17.5	dB	*1
Noise Figure HG	Noise Figure HG NFHb		_	1.3	1.9	dB	*1
IIP3 +10 MHz offset HG	IIP3H1b	f1 = fRXb + 10 MHz f2 = fRXb + 20 MHz Input 2 signals (f1, f2)	6.5	10.0	_	dBm	*1
IIP3 -10 MHz offset HG	IIP3H2b	f1 = fRXb - 10 MHz f2 = fRXb - 20 MHz Input 2 signals (f1, f2)	6.5	10.0	_	dBm	*1
Input P1dB	IP1dBHb	_	-15.0	-10.0	_	dBm	*1
Reverse Isolation HG	ISOHb	_	_	-30.0	-25.0	dB	*1
Input Return Loss HG	S11Hb	_	4.0	6.0	_	dB	*1
Output Return Loss HG	S22Hb	_	6.5	9.0	_	dB	*1
LNA AC electrical characteristics	(Low Gain	Mode)	•				
Power Gain LG	GLb	PRXb = -20 dBm	-9.5	-7.5	-5.5	dB	*1
Noise Figure LG	NFLb	_	_	7.5	10.0	dB	*1
IIP3 +10 MHz offset LG	IIP3L1b	f1 = fRXb + 10 MHz f2 = fRXb + 20 MHz PRXb = -10 dBm Input 2 signals (f1, f2)	20.0	24.0	_	dBm	*1
Reverse Isolation LG	ISOLb	_	-9.5	-7.5	-5.5	dB	*1
Input Return Loss LG	S11Lb	_	3.5	5.0		dB	*1
Output Return Loss LG	S22Lb	_	13.0	20.0		dB	*1

Note) *1 : Checked by design, not production tested.



Note) Vcc = 2.65 V to 2.95 V

Ta = -20°C to 70°C, CW unless otherwise specified.

Performance based on application circuit 1 on page 10.

	Parameter	Cumbal	Symbol Conditions		Reference values			Note
	Farameter			Min	Тур	Max	Unit	Note
DC	DC electrical characteristics							
	Supply current (High Gain Mode)	IccHT	Vcc current at High Gain mode No input signal	_	10	14.5	mA	*1
	Supply current (Low Gain Mode)	IccLT	Vcc current at Low Gain mode No input signal		1	12	μА	*1
	CNT current (High Gain Mode)	IcntHT	Current at CNT Pin Voltage at CNT Pin = 2.80 V	_	2	40	μА	*1
	CNT current (Low Gain Mode)	IcntLT	Current at CNT Pin Voltage at CNT Pin = 0 V	_	1	15	μΑ	*!

Note) *1 : Checked by design, not production tested.



Note) Vcc = 2.65 V to 2.95 V

Ta = -20°C to 70°C, fRXa= 2110MHz, 2132.5MHz, 2155MHz, PRXa =-30 dBm, CW unless otherwise specified. Performance based on application circuit 1 on page 10.

	Description	0	O and distance	Refe	rence va	alues	l lni4	Note
	Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
LNA	.NA AC electrical characteristics (High Gain Mode)							
	Power Gain HG	GHTa	Та —		15.5	18.5	dB	*1
	Noise Figure HG	NFHTa	_	_	1.3	2.2	dB	*1
	IIP3 +10 MHz offset HG	IIP3H1Ta	f1 = fRXa + 10 MHz f2 = fRXa + 20 MHz Input 2 signals (f1, f2)	4.5	9.5	_	dBm	*1
	IIP3 -10 MHz offset HG		f1 = fRXa - 10 MHz f2 = fRXa - 20 MHz Input 2 signals (f1, f2)	4.5	9.5	_	dBm	*1
	Input P1dB	IP1dBHTa	_	-17.0	-10.0	_	dBm	*1
LNA	AC electrical characteristics	(Low Gain	Mode)					
	Power Gain LG	GLTa	PRXa = −20 dBm	-10.5	-7.5	-4.5	dB	*1
	Noise Figure LG	NFLTa	_	_	7.5	11.5	dB	*1
	IIP3 +10 MHz offset LG		f1 = fRXa + 10 MHz f2 = fRXa + 20 MHz PRXa = -10 dBm Input 2 signals (f1, f2)	18.0	24.0	_	dBm	*1

Note) *1 : Checked by design, not production tested.



Note) Vcc = 2.65 V to 2.95 V

Ta = -20°C to 70°C, fRXb = 1930MHz, 1960MHz, 1990MHz, PRXb = -30 dBm, CW unless otherwise specified. Performance based on application circuit 2 on page 10.

	D	0	O and distance	Refe	rence va	lues	Unit	Note
	Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
LNA	A AC electrical characteristics	(High Gain	Mode)					
	Power Gain HG	GHTb	GHTb —		15.5	18.5	dB	*1
	Noise Figure HG	NFHTb	_	_	1.3	2.2	dB	*1
	IIP3 +10 MHz offset HG	IIP3H1Tb	f1 = fRXb + 10 MHz f2 = fRXb + 20 MHz Input 2 signals (f1, f2)	5.0	10.0	_	dBm	*1
	IIP3 -10 MHz offset HG	IIP3H2Tb	f1 = fRXb - 10 MHz f2 = fRXb - 20 MHz Input 2 signals (f1, f2)	5.0	10.0	_	dBm	*1
Ì	Input P1dB	IP1dBHTb	_	-17.0	-10.0	_	dBm	*1
LNA	A AC electrical characteristics	(Low Gain	Mode)					
	Power Gain LG	GLTb	PRXb = −20 dBm	-10.5	-7.5	-4.5	dB	*1
	Noise Figure LG	NFLTb	_	_	7.5	11.5	dB	*1
	IIP3 +10 MHz offset LG	IIP3LT1b	f1 = fRXb + 10 MHz f2 = fRXb + 20 MHz PRXb = -10 dBm Input 2 signals (f1, f2)	18.0	24.0	_	dBm	*1

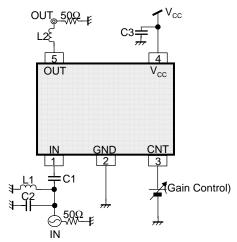
Note) *1 : Checked by design, not production tested.



APPLICATION INFORMATION (Continued) APPLICATION CIRCUIT

[Application Circuit 1 for 2.1 GHz Band]

TOP VIEW

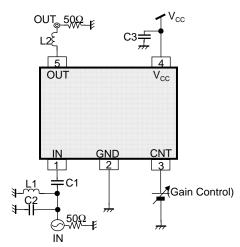


Components Size		Value	Value Part Number		
L1	0603	3.0 nH	LQP03T3N0B04	Murata	
L2	0603	5.6 nH	LQP03T5N6H04	Murata	
C1	0603	1000 pF	GRM033B11C102KD01	Murata	
C2	0603	2.0 pF	GJM0334C1E2R0BB01	Murata	
C3	0603	0.1 μF	GRM033B30J104KE18	Murata	

Notes) This application circuit is an example. The operation of mass production set is not guaranteed. You should perform enough evaluation and verification on the design of mass production set. You are fully responsible for the incorporation of the above application circuit and information in the design of your equipment.

[Application Circuit 2 for 1.9 GHz Band]

TOP VIEW

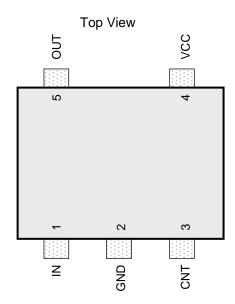


Components	Size	Value	Part Number	Vendor
L1	0603	3.6 nH	LQP03T6N0B04	Murata
L2	0603	5.6 nH	LQP03T5N6H04	Murata
C1	0603	1000 pF	GRM033B11C102KD01	Murata
C2	0603	2.0 pF	GJM0334C1E2R0BB01	Murata
C3	0603	0.1 μF	GRM033B30J104KE18	Murata

Notes) This application circuit is an example. The operation of mass production set is not guaranteed. You should perform enough evaluation and verification on the design of mass production set. You are fully responsible for the incorporation of the above application circuit and information in the design of your equipment.



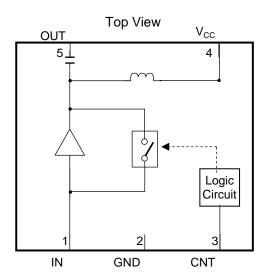
PIN CONFIGURATION



PIN FUNCTIONS

Pin No.	Pin name	Туре	Description
1	IN	Input	RF Input
2	GND	Ground	GND
3	CNT	Input	High Gain / Low Gain switch L: Low Gain Mode H: High Gain Mode
4	VCC	Power Supply	V _{cc}
5	OUT	Output	RF Output

FUNCTIONAL BLOCK DIAGRAM



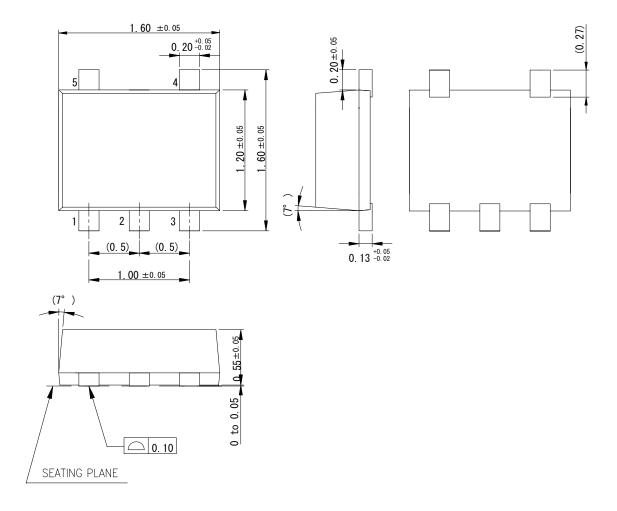
Notes) This circuit and these circuit constants show an example and do not guarantee the design as a mass-production set. This block diagram is for explaining functions. The part of the block diagram may be omitted, or it may be simplified.



PACKAGE INFORMATION (Reference Data)

Package Code:SSMINI-5DC

Unit:mm



Body Material : Br / Sb Free Epoxy Resin

Lead Material : Cu Alloy

Lead Finish Method : SnBi Plating



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